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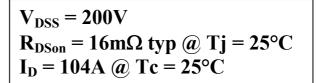


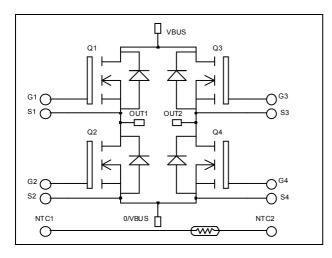






Full - Bridge MOSFET Power Module





O/VBUS

S2 🖟

G2 n

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

0 G3

VBUS

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		200	V
T	Continuous Dusin Comment	$T_c = 25$ °C	104	
I_D	Continuous Drain Current $T_c = 80$		77	A
I_{DM}	Pulsed Drain current		416	
V_{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		19	mΩ
P_{D}	Maximum Power Dissipation $T_c = 25^{\circ}C$		390	W
I_{AR}	Avalanche current (repetitive and non repetitive)		104	A
E _{AR}	Repetitive Avalanche Energy		50	mJ
E_{AS}	Single Pulse Avalanche Energy		3000	1113

OUT2

OUT1

NTC2 #

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
т	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 200V$ $T_j = 25^{\circ}C$			250	μΑ
$I_{ m DSS}$		$V_{GS} = 0V, V_{DS} = 160V$ $T_j = 125^{\circ}C$			1000	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 52A$		16	19	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 2.5 \text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

Dynamic Characteristics

•	Characteristic	Test Conditions	Min	Тур	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		7220		
C_{oss}	Output Capacitance	$V_{DS} = 25V$		2330		pF
C_{rss}	Reverse Transfer Capacitance	f=1MHz		146		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		140		
$Q_{\rm gs}$	Gate – Source Charge	$V_{Bus} = 100V$		53		nC
Q_{gd}	Gate – Drain Charge	$I_D=104A$		67		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C		32		
T_{r}	Rise Time	$V_{GS} = 15V$		64		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 133 \text{V}$ $I_{\text{D}} = 104 \text{A}$		88		ns
T_{f}	Fall Time	$R_G = 5\Omega$		116		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		849		т
E_{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 133V$ $I_D = 104A, R_G = 5\Omega$		929		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		936		т
E _{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 133V$ $I_D = 104A, R_G = 5\Omega$		986		μJ

Source - Drain diode ratings and characteristics

Source - Drain diode ratings and characteristics							
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_S	Continuous Source current (Body diode)		$Tc = 25^{\circ}C$			104	A
18		Ţ	$Tc = 80^{\circ}C$			77	Λ
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -104A$				1.3	V
dv/dt	Peak Diode Recovery •					5	V/ns
t	Reverse Recovery Time		$T_j = 25^{\circ}C$			230	ns
t_{rr}	Reverse Recovery Time	$I_S = -104A$ $V_R = 133V$	$T_j = 125$ °C			450	115
Q _{rr}	Reverse Recovery Charge	$di_S/dt = 100A/\mu s$	$T_j = 25^{\circ}C$	(0.9		μC
	Reverse Recovery Charge	·	$T_j = 125$ °C		3.4		μС

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \leq \text{--} 104 A \qquad \text{di/dt} \leq 700 A/\mu s \qquad V_R \leq V_{DSS} \qquad T_j \leq 150 ^{\circ} C$



Thermal and package characteristics

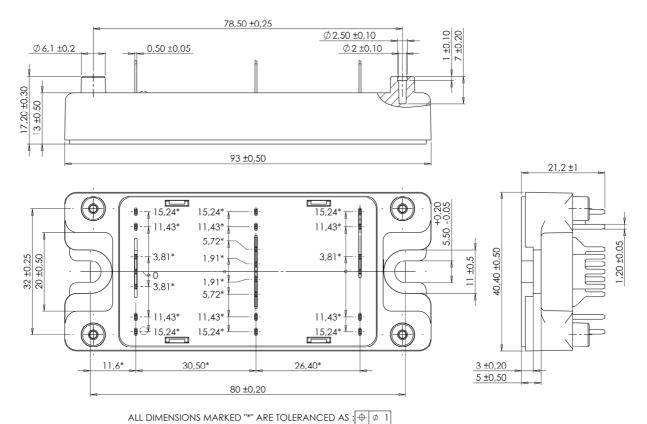
Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance					0.32	°C/W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range		-40		150		
T_{STG}	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight				160	g	

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature at T

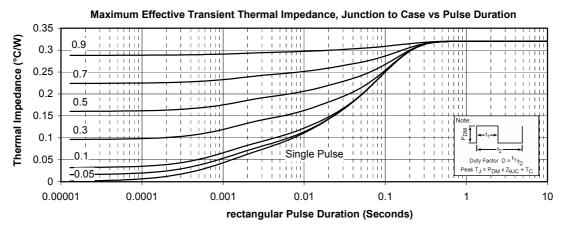
SP4 Package outline (dimensions in mm)

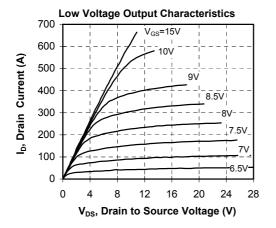


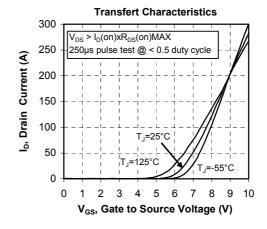
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

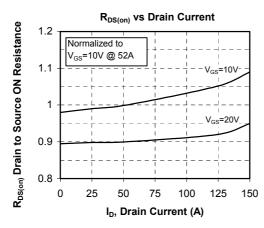


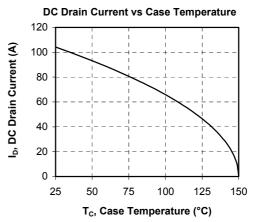
Typical Performance Curve



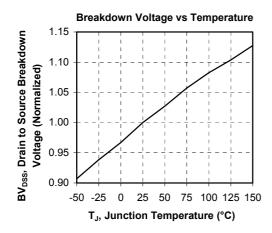


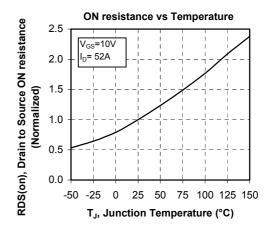


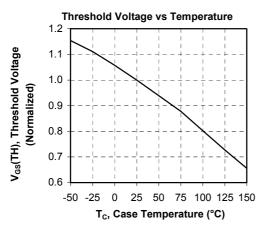


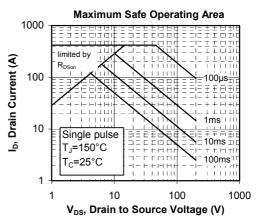


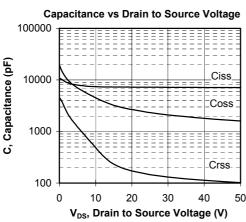


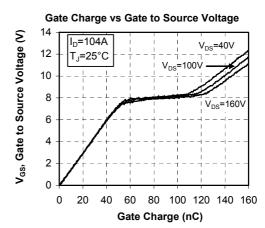




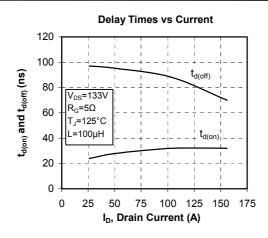


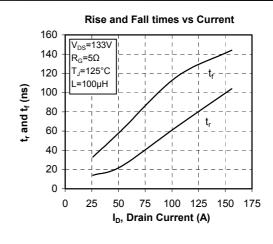


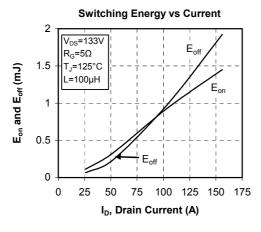


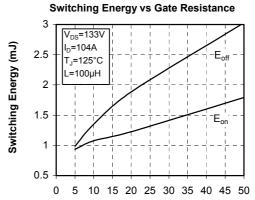




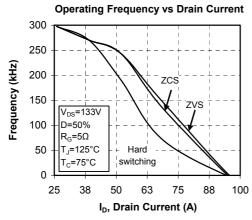


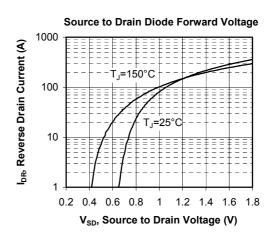






Gate Resistance (Ohms)





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